

FIG. 1

Reaction process of etching an SiN film with HF

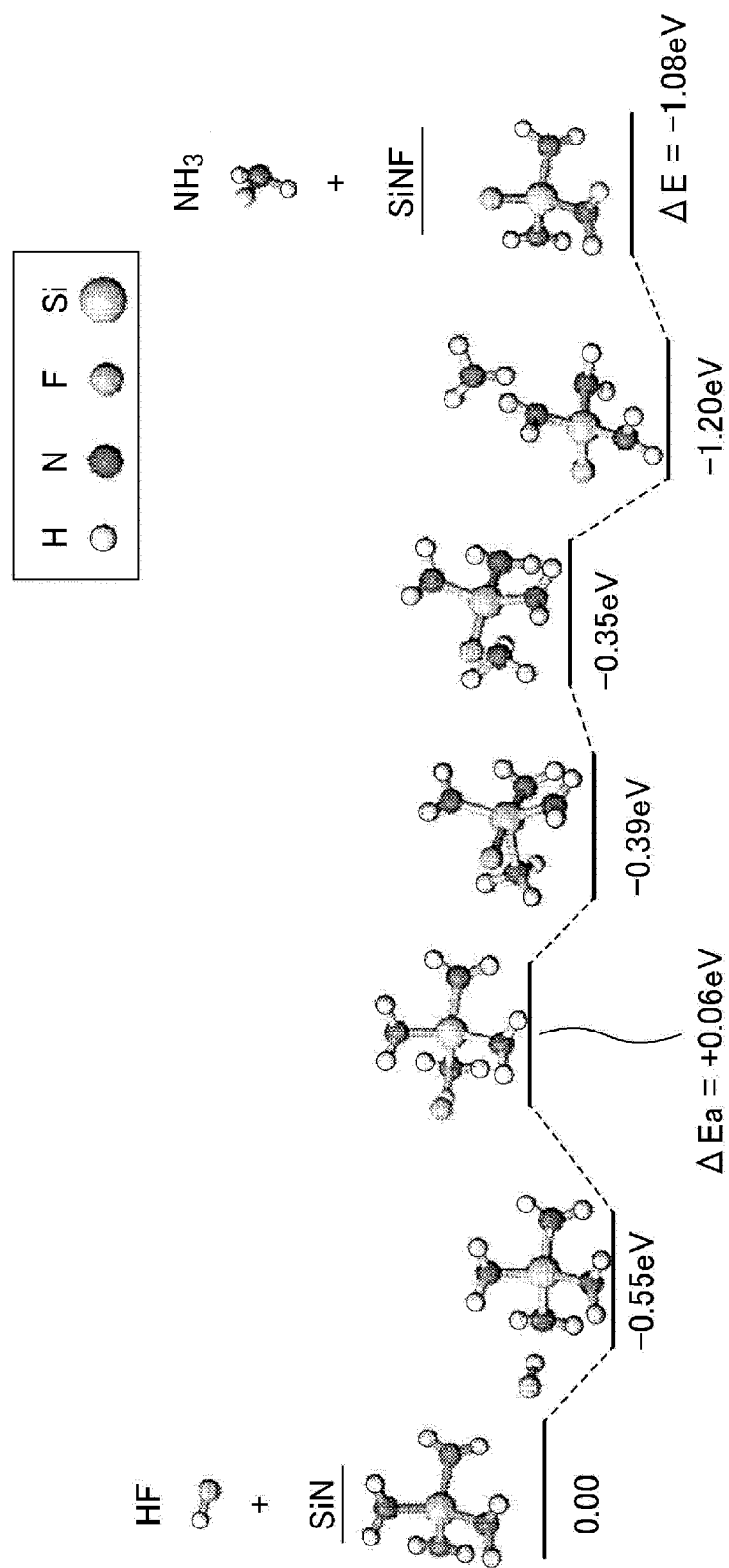
Activation energy $\Delta E_a = +0.06 \text{ eV}$ Generation energy $\Delta E = -1.08 \text{ eV}$

FIG. 2

Activation energy ΔE_a and generation energy ΔE in reaction process of etching SiN film with HF and reaction process of etching SiO_2 film with HF

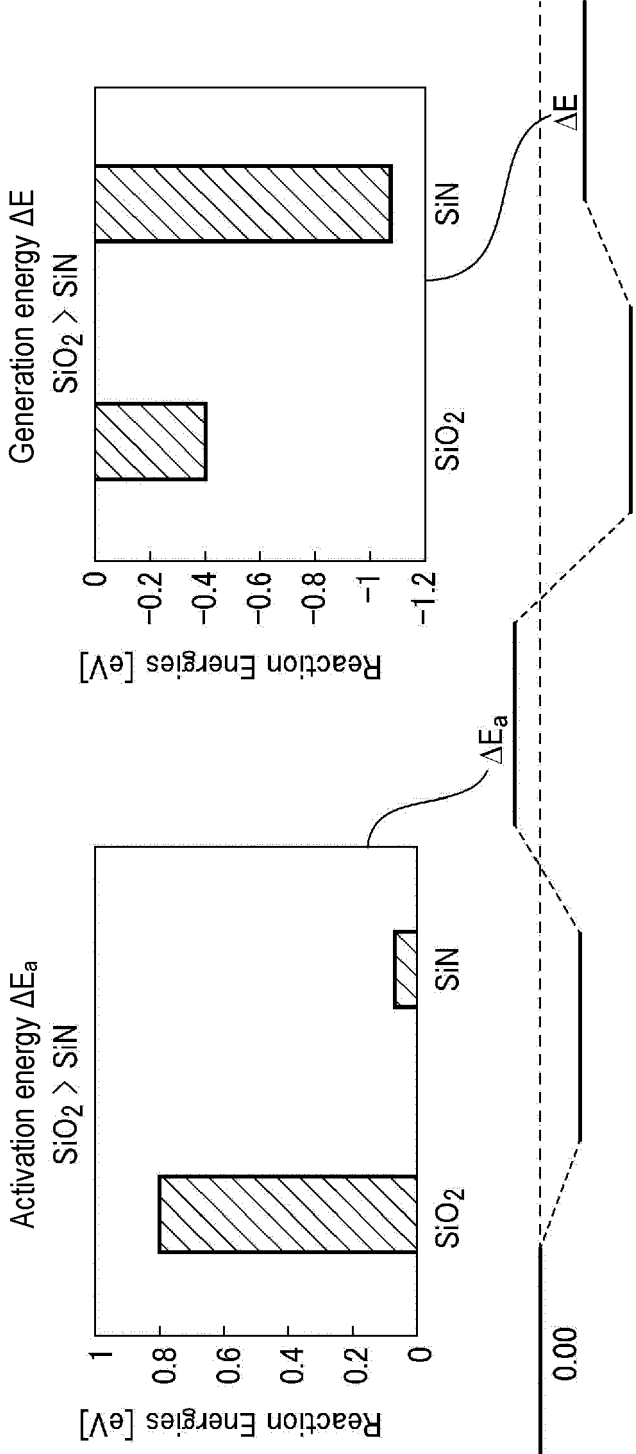


FIG. 3

10

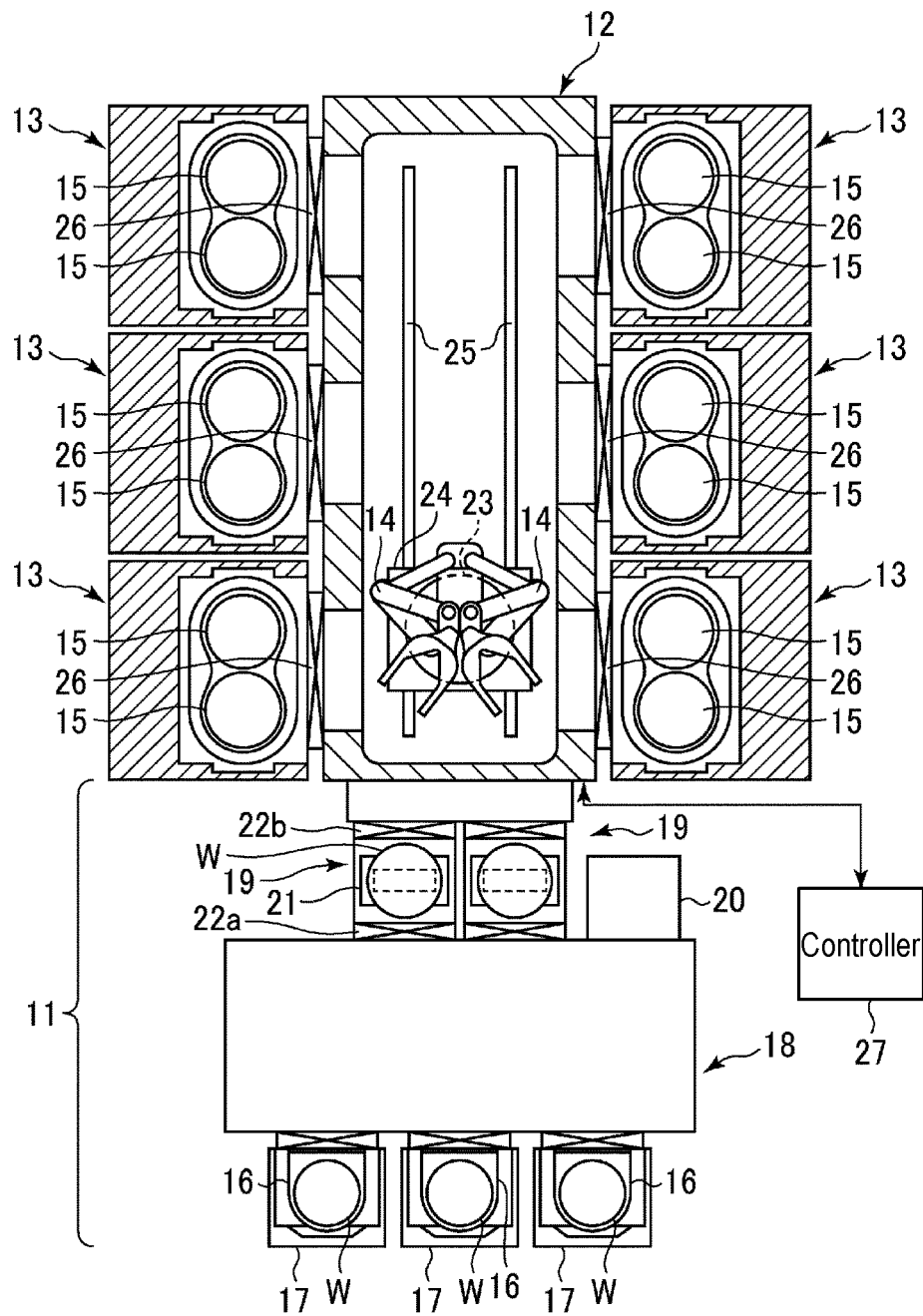


FIG. 4

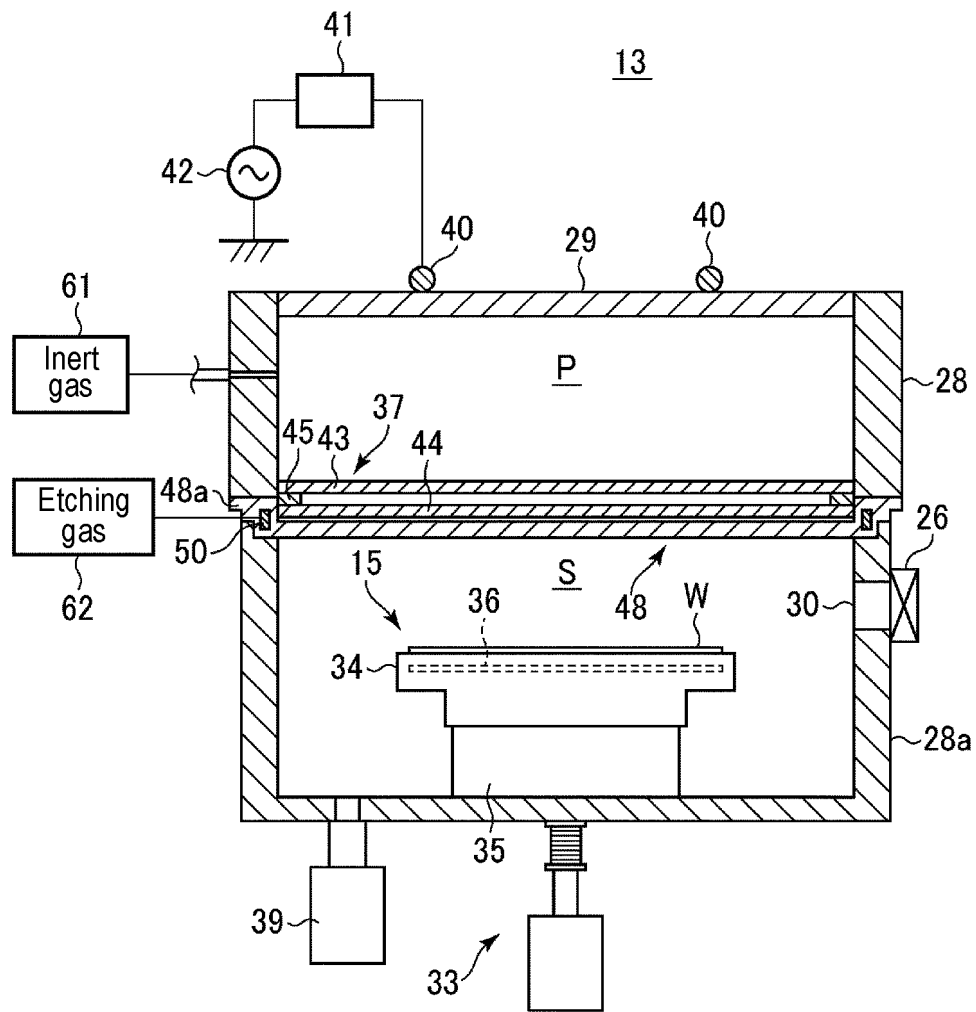


FIG. 5A

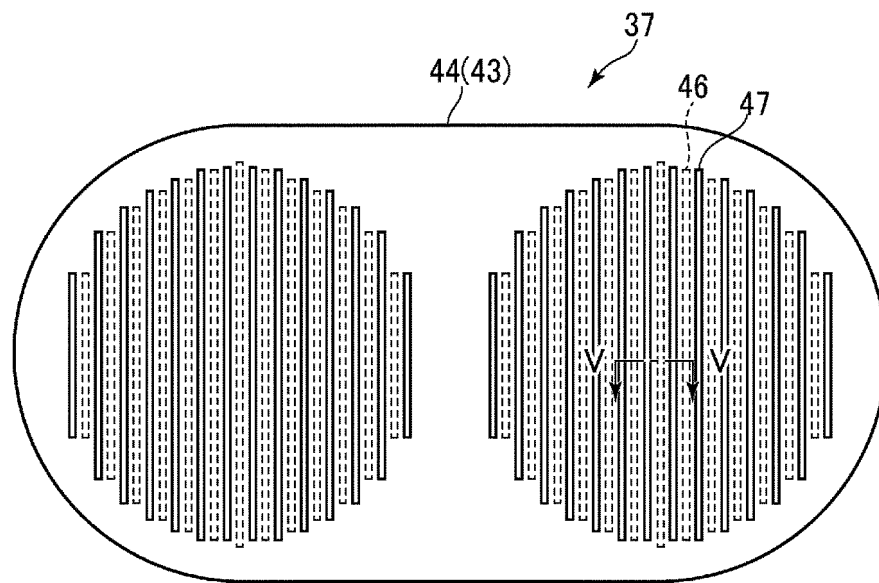


FIG. 5B

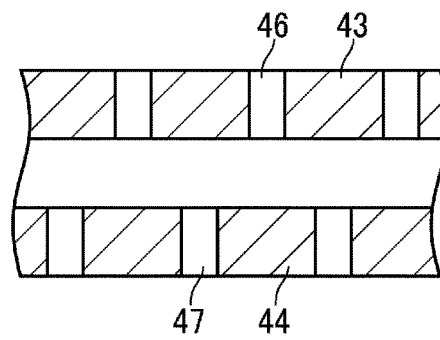


FIG. 6A

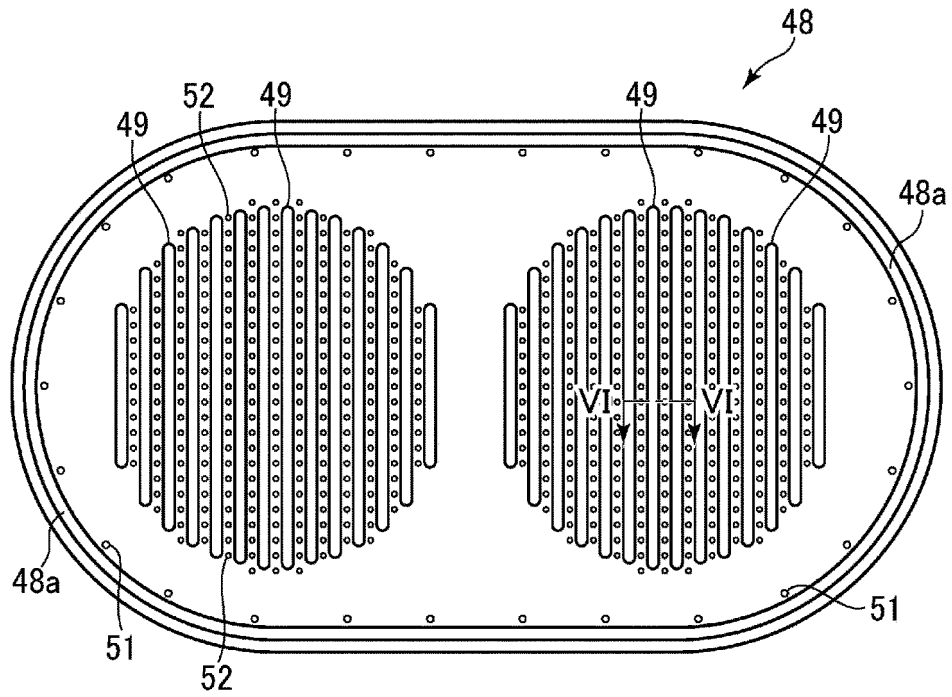


FIG. 6B

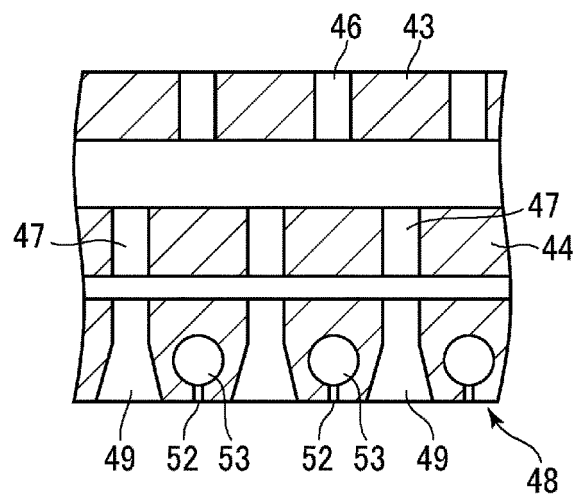


FIG. 7

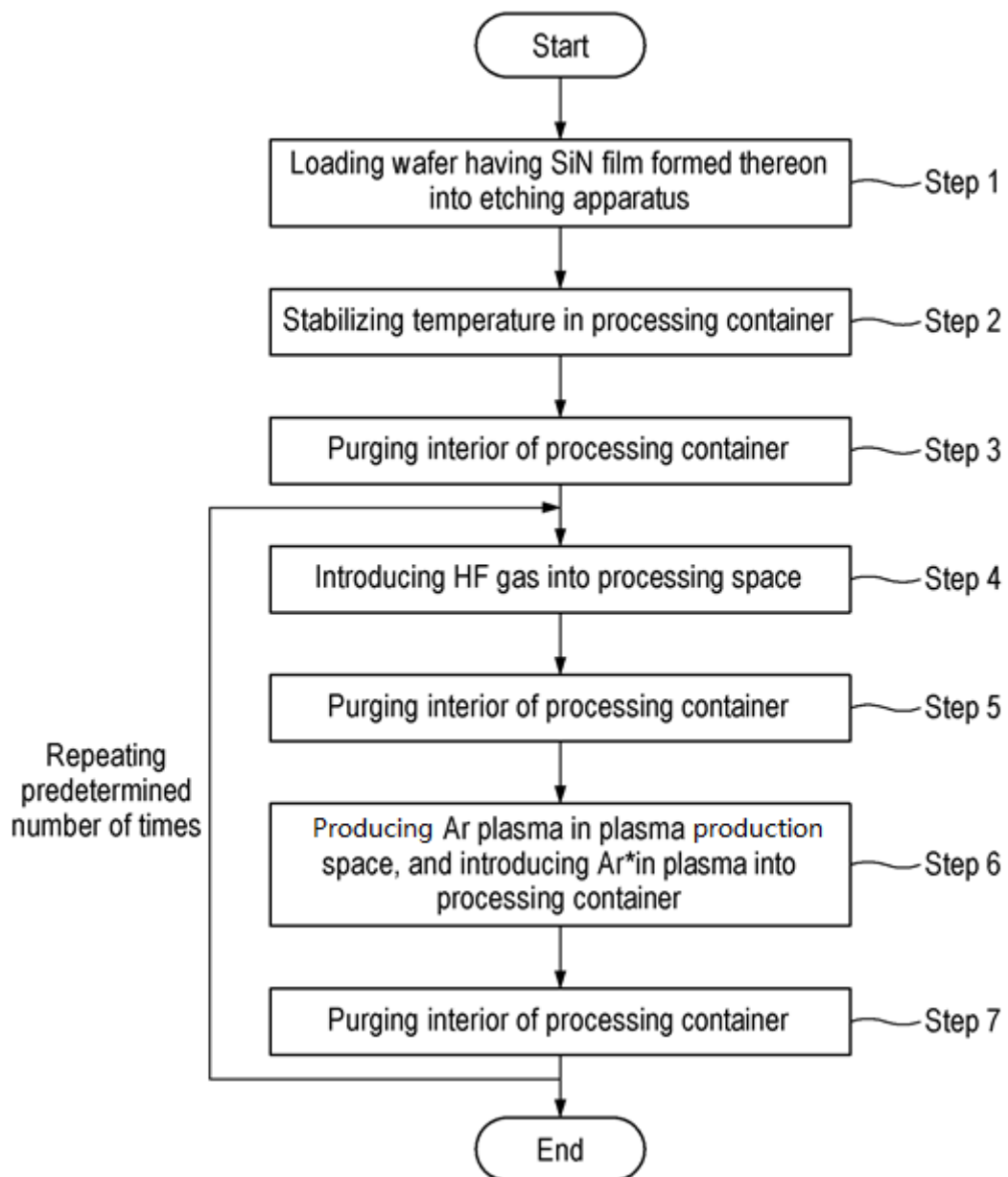


FIG. 8

